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		APPLICANT Seung-Hyun RHEE, et al.			
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U.S. PATENT DOCUMENTS					
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sub>2</sub> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS					
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See 2		Vincent ARNAL et al. "A Novel SiO <sub>2</sub> -Air Low K for Copper Dual Damascene Interconnect", Conference Proceedings ULSI XVI (2001) Materials Research Society pp. 71-77.			
See 2		B. SHIEH et al., "Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998			
See 2		B. P. SHIEH et al., "Integration and Reliability Issues for Low Capacitance Air-Gap Interconnect Structures", 1998 IEEE			
See 2		Vincent Arnal et al., "Optimization of CVD Dielectric Process to Achieve Reliable Ultra Low-k Air Gaps", Microelectronic Engineering 60 (2002) pp. 143-148			
EXAMINER Mahmoud		DATE CONSIDERED 12-23-05			

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